Dual N-Channel 60-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- Low thermal impedance
- Fast switching speed

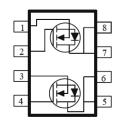
Typical Applications:

- DC/DC Conversion Circuits
- Motor Drives
- Power Routing

PRODUCT SUMMARY				
VDS (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
60	37 @ V _{GS} = 10V	19		
00	45 @ V _{GS} = 4.5V	17		

DFN5X6-8L





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			60	V		
Gate-Source Voltage		V _{GS}	±20	v		
	T _C =25°C		19	А		
Continuous Drain Current	T _C =70°C	- I-	15			
	T _A =25°C	I _D	6.8 ^a			
	T _A =70°C		5.4 ^a	~		
Pulsed Drain Current ^b	I _{DM}	30				
Continuous Source Current (Diode Conduction) ^a	ا _s	2.4				
	T _C =25°C		19	W		
Power Dissipation	T _C =70°C	P _D	12			
	T _A =25°C	'D	2.5 ^a			
	T _A =70°C		1.6 ^a			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	R _{eja}	50	°C/W			
	Steady State	INθJA	90				
Maximum Junction-to-Case	Steady State	$R_{ extsf{ heta}JC}$	6.5				

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature
- c. Package limited

Electrical Characteristics

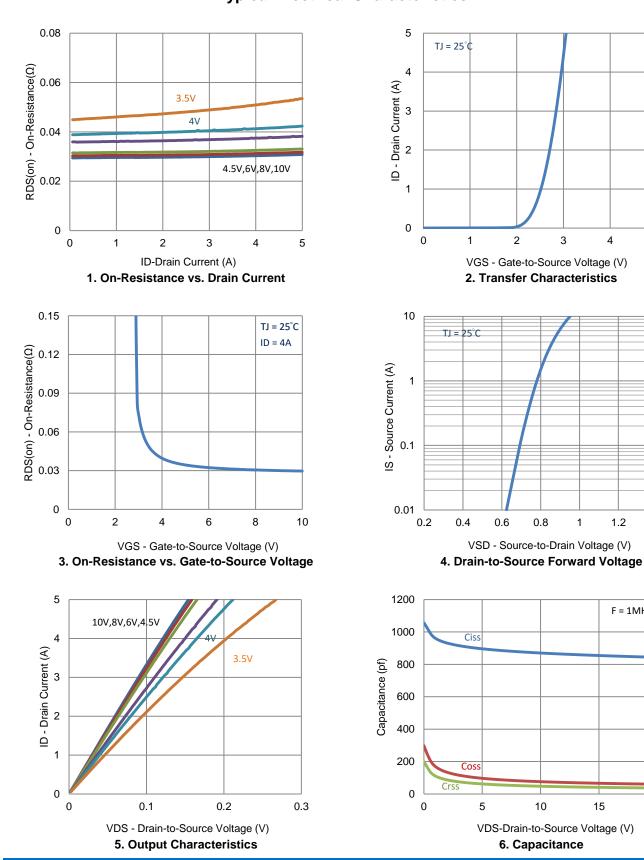
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$	1		1	uA	
	IDSS	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	12			А	
	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 4 \text{ A}$			37		
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 3 \text{ A}$			45	mΩ	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 4 \text{ A}$		8		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 1.2 \text{ A}, V_{GS} = 0 \text{ V}$		0.79		V	
		Dynamic ^b					
Total Gate Charge	Q _g	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$		8			
Gate-Source Charge	Q _{gs}	$V_{\rm DS} = 30$ V, $V_{\rm GS} = 4.5$ V, $I_{\rm D} = 4$ A		3.1		nC	
Gate-Drain Charge	Q_gd			2.5			
Turn-On Delay Time	t _{d(on)}	V _{DS} = 30 V, R _I = 7.5 Ω,		5			
Rise Time	t _r	$V_{\rm DS} = 30$ V, $N_{\rm L} = 7.5$ Ω, $I_{\rm D} = 4$ A,		8		ns	
Turn-Off Delay Time	t _{d(off)}	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		36			
Fall Time	t _f	$V_{\text{GEN}} = 10$ V, $V_{\text{GEN}} = 0.22$		9			
Input Capacitance	C _{iss}			854			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		66		рF	
Reverse Transfer Capacitance	C _{rss}			41			

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

5



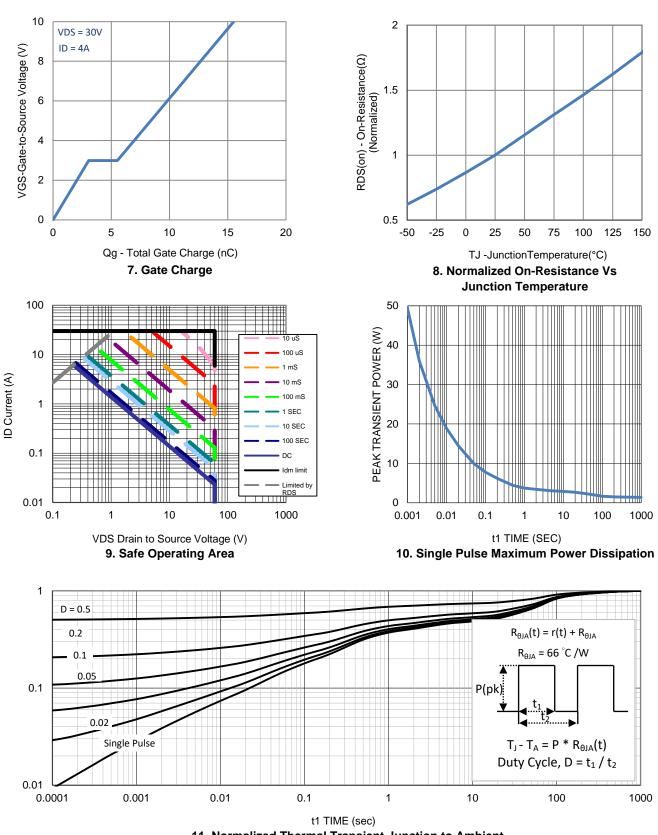
Typical Electrical Characteristics

1.2

F = 1MHz

1.4

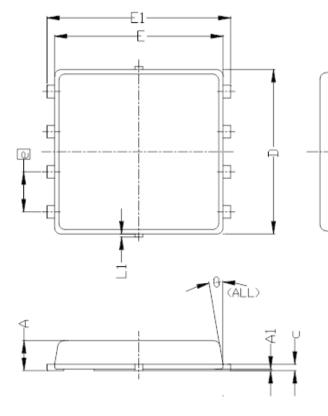
20

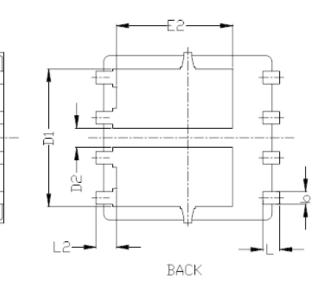


Typical Electrical Characteristics

11. Normalized Thermal Transient Junction to Ambient

Package Information





	DIMENS	TONS IN MILLI	METEDS	DIM	ENSIONS IN IN	TUES	
SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0.15	0.20	0.25	0.006	0.008	0.010	
D	5. 20 BSC			0.205 BSC			
D1	4.35 BSC			0.171 BSC			
E	5.55 BSC			0.219 BSC			
E1	6.05 BSC		0.238 BSC				
E2	3.62 BSC		0.143 BSC				
e	1.27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	